

Silicon Standard Recovery Diode

 $V_{RRM} = 100\text{ V} - 1200\text{ V}$
 $I_F = 6\text{ A}$

Features

- High Surge Capability
- Types up to 1200 V V_{RRM}

DO-4 Package

Maximum ratings, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	S6B (R)	S6D (R)	S6G (R)	S6J (R)	Unit
Repetitive peak reverse voltage	V_{RRM}		100	200	400	600	V
RMS reverse voltage	V_{RMS}		70	140	280	420	V
DC blocking voltage	V_{DC}		100	200	400	600	V
Continuous forward current	I_F	$T_C \leq 160\text{ }^{\circ}\text{C}$	6	6	6	6	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ }^{\circ}\text{C}$, $t_p = 8.3\text{ ms}$	167	167	167	167	A
Operating temperature	T_j		-65 to 175	-65 to 175	-65 to 175	-65 to 175	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-65 to 200	-65 to 200	-65 to 200	-65 to 200	$^{\circ}\text{C}$

Electrical characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	S6B (R)	S6D (R)	S6G (R)	S6J (R)	Unit
Diode forward voltage	V_F	$I_F = 6\text{ A}$, $T_j = 25\text{ }^{\circ}\text{C}$	1.1	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 100\text{ V}$, $T_j = 25\text{ }^{\circ}\text{C}$	10	10	10	10	μA
		$V_R = 100\text{ V}$, $T_j = 175\text{ }^{\circ}\text{C}$	12	12	12	12	mA

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		2.50	2.50	2.50	2.50	$^{\circ}\text{C/W}$
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Figure .1-Typical Forward Characteristics

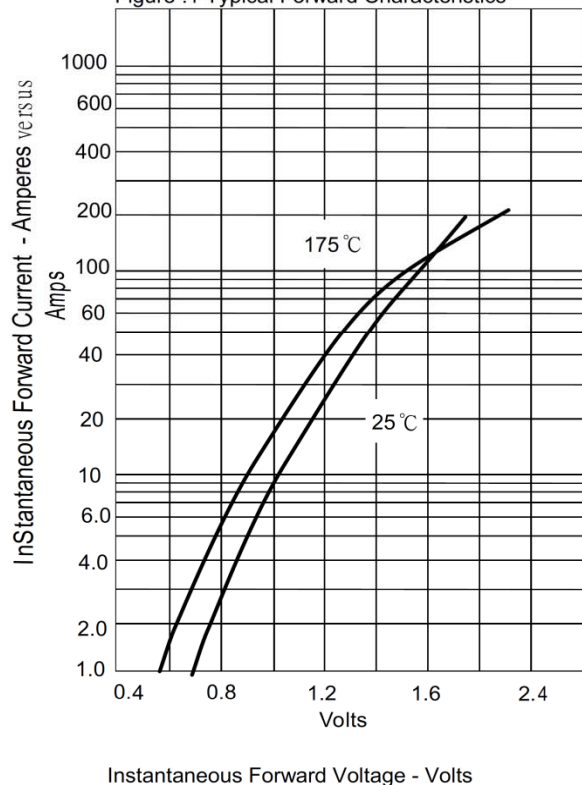


Figure .2-Forward Derating Curve

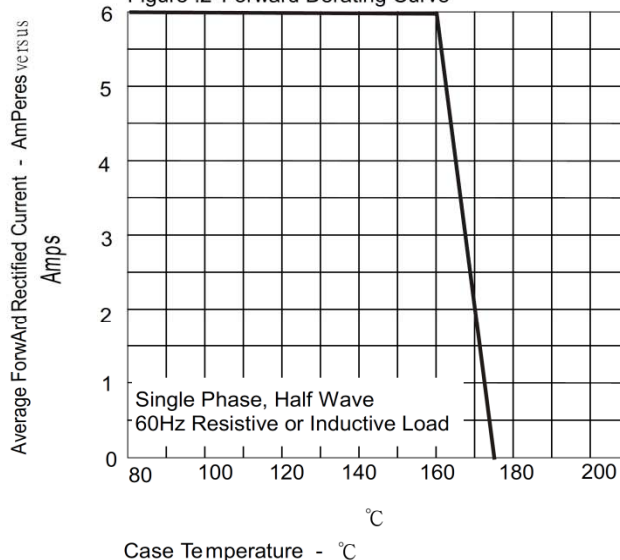


Figure .3-Peak Forward Surge Current

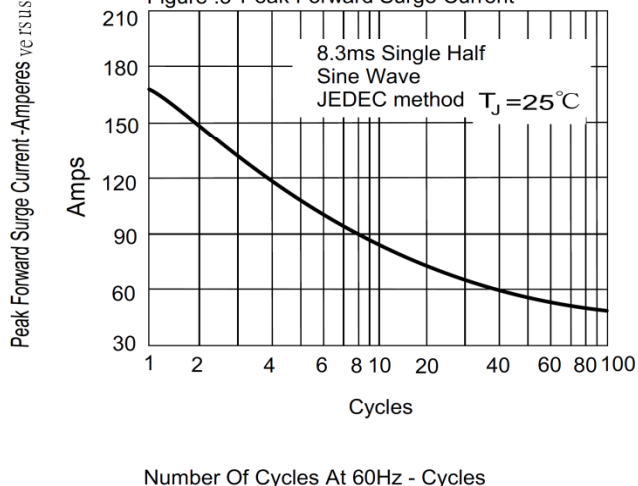


Figure .4-Typical Reverse Characteristics

